4-bit dual supply translating transceiver with configurable voltage translation; 3-state

Rev. 2 — 17 December 2015

**Product data sheet** 

### 1. General description

The 74AVCH4T245-Q100 is a 4-bit, dual supply transceiver that enables bidirectional level translation. The device can be used as two 2-bit transceivers or as a 4-bit transceiver. It features two 2-bit input-output ports (nAn and nBn), a direction control input (nDIR), an output enable input (nOE) and dual supply pins ( $V_{CC(A)}$  and  $V_{CC(B)}$ ). Both  $V_{CC(A)}$  and  $V_{CC(B)}$  can be supplied with any voltage between 0.8 V and 3.6 V. This feature makes the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V). Pins nAn, nOE and nDIR are referenced to  $V_{CC(A)}$  and pins nBn are referenced to  $V_{CC(B)}$ . A HIGH on nDIR allows transmission from nAn to nBn and a LOW on nDIR allows transmission from nBn to nAn. The output enable input (nOE) can be used to disable the outputs so the buses are effectively isolated.

The device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In suspend mode when either  $V_{CC(A)}$  or  $V_{CC(B)}$  are at GND level, both nAn and nBn outputs are in the high-impedance OFF-state. The bus hold circuitry on the powered-up side always stays active.

The 74AVCH4T245-Q100 has active bus hold circuitry which is provided to hold unused or floating data inputs at a valid logic level. This feature eliminates the need for external pull-up or pull-down resistors.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

### 2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Wide supply voltage range:
  - V<sub>CC(A)</sub>: 0.8 V to 3.6 V
  - V<sub>CC(B)</sub>: 0.8 V to 3.6 V
- Complies with JEDEC standards:
  - JESD8-12 (0.8 V to 1.3 V)
  - JESD8-11 (0.9 V to 1.65 V)
  - JESD8-7 (1.2 V to 1.95 V)
  - JESD8-5 (1.8 V to 2.7 V)
  - JESD8-B (2.7 V to 3.6 V)

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- ESD protection:
  - ◆ MIL-STD-883, method 3015 Class 3B exceeds 8000 V
  - ◆ HBM JESD22-A114E Class 3B exceeds 8000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pf, R = 0 Ω)
- Maximum data rates:
  - ◆ 380 Mbit/s (≥ 1.8 V to 3.3 V translation)
  - ◆ 200 Mbit/s (≥ 1.1 V to 3.3 V translation)
  - ◆ 200 Mbit/s (≥ 1.1 V to 2.5 V translation)
  - ◆ 200 Mbit/s (≥ 1.1 V to 1.8 V translation)
  - ◆ 150 Mbit/s (≥ 1.1 V to 1.5 V translation)
  - ◆ 100 Mbit/s (≥ 1.1 V to 1.2 V translation)
- Suspend mode
- Bus hold on data inputs
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- I<sub>OFF</sub> circuitry provides partial Power-down mode operation
- Multiple package options

### 3. Ordering information

#### Table 1.Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74AVCH4T245D-Q100	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1					
74AVCH4T245PW-Q100	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1					
74AVCH4T245BQ-Q100	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body $2.5 \times 3.5 \times 0.85$ mm	SOT763-1					

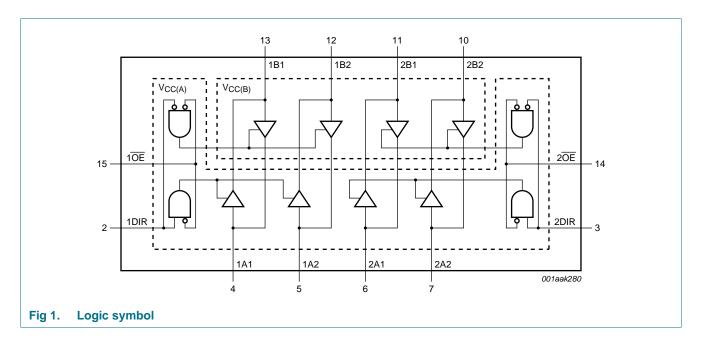
### 4. Marking

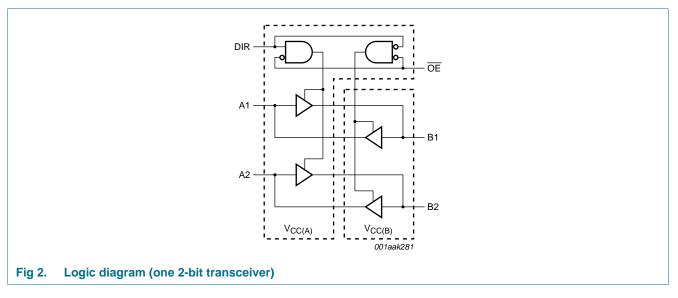
#### Table 2.Marking codes

Type number	Marking code
74AVCH4T245D-Q100	74AVCH4T245D
74AVCH4T245PW-Q100	CH4T245
74AVCH4T245BQ-Q100	H4T245

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### 5. Functional diagram

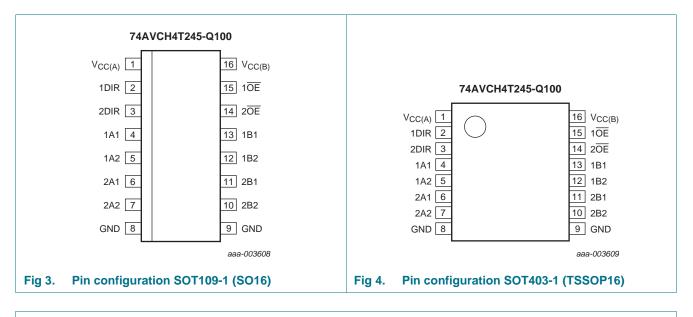


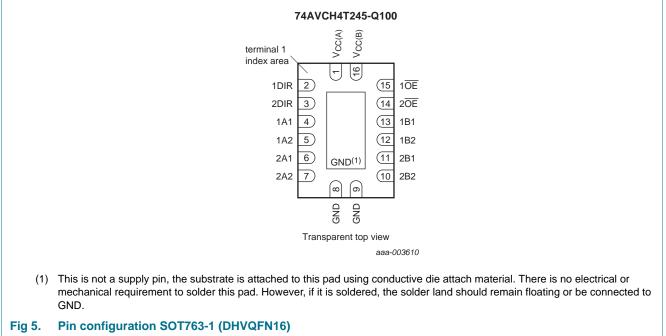


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### 6. Pinning information

### 6.1 Pinning





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### 6.2 Pin description

Symbol	Pin	Description
V <sub>CC(A)</sub>	1	supply voltage A (nAn, $n\overline{OE}$ and nDIR inputs are referenced to V <sub>CC(A)</sub> )
1DIR, 2DIR	2, 3	direction control
1A1, 1A2	4, 5	data input or output
2A1, 2A2	6, 7	data input or output
GND <sup>[1]</sup>	8, 9	ground (0 V)
2B2, 2B1	10, 11	data input or output
1B2, 1B1	12, 13	data input or output
2 <u>0E</u> , 1 <u>0E</u>	14, 15	output enable input (active LOW)
V <sub>CC(B)</sub>	16	supply voltage B (nBn inputs are referenced to V <sub>CC(B)</sub> )

[1] All GND pins must be connected to ground (0 V).

### 7. Functional description

#### Table 4.Function table

Supply voltage	Input		Input/output <sup>[3]</sup>	
V <sub>CC(A)</sub> , V <sub>CC(B)</sub>	nOE <sup>[2]</sup>	nDIR <sup>[2]</sup>	nAn <sup>[2]</sup>	nBn <sup>[2]</sup>
0.8 V to 3.6 V	L	L	nAn = nBn	input
0.8 V to 3.6 V	L	Н	input	nBn = nAn
0.8 V to 3.6 V	Н	Х	Z	Z
GND[ <u>3]</u>	X	Х	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] The nAn, nDIR and n $\overline{OE}$  input circuit is referenced to V<sub>CC(A)</sub>; The nBn input circuit is referenced to V<sub>CC(B)</sub>.

[3] If at least one of  $V_{CC(A)}$  or  $V_{CC(B)}$  is at GND level, the device goes into suspend mode.

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### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC(A)</sub>	supply voltage A			-0.5	+4.6	V
V <sub>CC(B)</sub>	supply voltage B			-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V		-50	-	mA
VI	input voltage		[1]	-0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V		-50	-	mA
Vo	output voltage	Active mode	<u>[1][2][3]</u>	-0.5	V <sub>CCO</sub> + 0.5	V
		Suspend or 3-state mode	[1]	-0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to $V_{CCO}$	[2]	-	±50	mA
I <sub>CC</sub>	supply current	per $V_{CC(A)}$ or $V_{CC(B)}$ pin		-	100	mA
I <sub>GND</sub>	ground current	per GND pin		-100	-	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$				
		SO16, TSSOP16 and DHVQFN16	[4]	-	500	mW

[1] The minimum input voltage ratings and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] V<sub>CCO</sub> is the supply voltage associated with the output port.

[3]  $V_{CCO}$  + 0.5 V should not exceed 4.6 V.

[4] For SO16 package: above 70 °C the value of P<sub>tot</sub> derates linearly at 8 mW/K.
 For TSSOP16 package: above 60 °C the value of P<sub>tot</sub> derates linearly at 5.5 mW/K.
 For DHVQFN16 package: above 60 °C the value of P<sub>tot</sub> derates linearly at 4.5 mW/K.

### 9. Recommended operating conditions

#### Table 6. Recommended operating conditions

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC(A)</sub>	supply voltage A			0.8	3.6	V
V <sub>CC(B)</sub>	supply voltage B			0.8	3.6	V
VI	input voltage			0	3.6	V
Vo	output voltage	Active mode	<u>[1]</u>	0	V <sub>CCO</sub>	V
		Suspend or 3-state mode		0	3.6	V
T <sub>amb</sub>	ambient temperature			-40	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CCI} = 0.8 V \text{ to } 3.6 V$	[2]	-	5	ns/V

[1]  $V_{CCO}$  is the supply voltage associated with the output port.

[2]  $V_{CCI}$  is the supply voltage associated with the input port.

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### **10. Static characteristics**

#### Table 7. Typical static characteristics at $T_{amb} = 25 \text{ °C} [1][2]$

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$					
		$I_{O} = -1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$		-	0.69	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		$I_{O}$ = 1.5 mA; $V_{CC(A)} = V_{CC(B)} = 0.8 V$		-	0.07	-	V
lı	input leakage current	nDIR, n $\overline{OE}$ input; V <sub>I</sub> = 0 V or 3.6 V; V <sub>CC(A)</sub> = V <sub>CC(B)</sub> = 0.8 V to 3.6 V		-	±0.025	±0.25	μA
I <sub>BHL</sub>	bus hold LOW current	A or B port; $V_I = 0.42$ V; $V_{CC(A)} = V_{CC(B)} = 1.2$ V	[3]	-	26	-	μA
I <sub>BHH</sub>	bus hold HIGH current	A or B port; $V_I = 0.78$ V; $V_{CC(A)} = V_{CC(B)} = 1.2$ V	<u>[4]</u>	-	-24	-	μA
I <sub>BHLO</sub>	bus hold LOW overdrive current	A or B port; $V_{CC(A)} = V_{CC(B)} = 1.2 V$	[5]	-	27	-	μA
I <sub>BHHO</sub>	bus hold HIGH overdrive current	A or B port; $V_{CC(A)} = V_{CC(B)} = 1.2 V$	[6]	-	-26	-	μΑ
I <sub>OZ</sub>	OFF-state output current	A or B port; $V_0 = 0$ V or $V_{CCO}$ ; $V_{CC(A)} = V_{CC(B)} = 3.6$ V	[7]	-	±0.5	±2.5	μA
		suspend mode A port; $V_O = 0 V \text{ or } V_{CCO}$ ; $V_{CC(A)} = 3.6 V$ ; $V_{CC(B)} = 0 V$	[7]	-	±0.5	±2.5	μA
		suspend mode B port; $V_O = 0 V$ or $V_{CCO}$ ; $V_{CC(A)} = 0 V$ ; $V_{CC(B)} = 3.6 V$	[7]	-	±0.5	±2.5	μA
I <sub>OFF</sub>	power-off leakage current	A port; V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC(A)</sub> = 0 V; V <sub>CC(B)</sub> = 0.8 V to 3.6 V		-	±0.1	±1	μA
		B port; V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC(B)</sub> = 0 V; V <sub>CC(A)</sub> = 0.8 V to 3.6 V		-	±0.1	±1	μA
CI	input capacitance	nDIR, n $\overline{OE}$ input; V <sub>1</sub> = 0 V or 3.3 V; V <sub>CC(A)</sub> = V <sub>CC(B)</sub> = 3.3 V		-	1.0	-	pF
C <sub>I/O</sub>	input/output capacitance	A and B port; $V_O = 3.3$ V or 0 V; $V_{CC(A)} = V_{CC(B)} = 3.3$ V		-	4.0	-	pF

[1]  $V_{CCO}$  is the supply voltage associated with the output port.

[2]  $V_{CCI}$  is the supply voltage associated with the data input port.

[3] The bus hold circuit can sink at least the minimum low sustaining current at maximum V<sub>IL</sub>. I<sub>BHL</sub> should be measured after lowering V<sub>I</sub> to GND and then raising it to maximum V<sub>IL</sub>.

[4] The bus hold circuit can source at least the minimum high sustaining current at minimum  $V_{IH}$ .  $I_{BHH}$  should be measured after raising  $V_{I}$  to  $V_{CC}$  and then lowering it to minimum  $V_{IH}$ .

[5] An external driver must source at least  $I_{\mbox{\scriptsize BHLO}}$  to switch this node from LOW to HIGH.

[6] An external driver must sink at least  $I_{BHHO}$  to switch this node from HIGH to LOW.

[7] For I/O ports, the parameter I<sub>OZ</sub> includes the input leakage current.

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#### Table 8. Static characteristics [1][2]

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C te	o +85 °C	–40 °C to	• +125 °C	Unit
			Min	Мах	Min	Max	-
V <sub>IH</sub>	HIGH-level	data input					
	input voltage	V <sub>CCI</sub> = 0.8 V	0.70V <sub>CCI</sub>	-	0.70V <sub>CCI</sub>	-	V
		V <sub>CCI</sub> = 1.1 V to 1.95 V	$0.65V_{CCI}$	-	0.65V <sub>CCI</sub>	-	V
		$V_{CCI} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	1.6	-	V
		V <sub>CCI</sub> = 3.0 V to 3.6 V	2	-	2	-	V
		nDIR, nOE input					
		V <sub>CC(A)</sub> = 0.8 V	0.70V <sub>CC(A)</sub>	-	0.70V <sub>CC(A)</sub>	-	V
		V <sub>CC(A)</sub> = 1.1 V to 1.95 V	0.65V <sub>CC(A)</sub>	-	0.65V <sub>CC(A)</sub>	-	V
		V <sub>CC(A)</sub> = 2.3 V to 2.7 V	1.6	-	1.6	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	2	-	2	-	V
VIL	LOW-level	data input					
	input voltage	V <sub>CCI</sub> = 0.8 V	-	0.30V <sub>CCI</sub>	-	0.30V <sub>CCI</sub>	V
		V <sub>CCI</sub> = 1.1 V to 1.95 V	-	0.35V <sub>CCI</sub>	-	0.35V <sub>CCI</sub>	V
		$V_{CCI} = 2.3 \text{ V to } 2.7 \text{ V}$	-	0.7	-	0.7	V
		$V_{CCI} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	0.8	-	0.8	V
		nDIR, nOE input					
		V <sub>CC(A)</sub> = 0.8 V	-	0.30V <sub>CC(A)</sub>	-	0.30V <sub>CC(A)</sub>	V
		V <sub>CC(A)</sub> = 1.1 V to 1.95 V	-	$0.35V_{CC(A)}$	-	0.35V <sub>CC(A)</sub>	V
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	-	0.7	-	0.7	V
		V <sub>CC(A)</sub> = 3.0 V to 3.6 V	-	0.8	-	0.8	V
/ <sub>ОН</sub>	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$					
	output voltage	$    I_O = -100 \ \mu \text{A}; \\ V_{CC(\text{A})} = V_{CC(\text{B})} = 0.8 \ \text{V to } 3.6 \ \text{V} $	V <sub>CCO</sub> – 0.1	-	V <sub>CCO</sub> – 0.1	-	V
		$I_{O} = -3 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	0.85	-	0.85	-	V
		$I_{O} = -6 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	1.05	-	1.05	-	V
		$I_{O} = -8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	1.2	-	1.2	-	V
		$I_{O} = -9 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	1.75	-	1.75	-	V
		$I_{O} = -12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3	-	2.3	-	V

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#### Static characteristics ...continued[1][2] Table 8.

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		–40 °C t	o +85 °C	–40 °C to +125 °C		Unit
				Min	Max	Min	Max	
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	output	I <sub>O</sub> = 100 μA;		-	0.1	-	0.1	V
	voltage	$V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$						
		I <sub>O</sub> = 3 mA;		-	0.25	-	0.25	V
		$V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$						
		$I_{O} = 6 \text{ mA};$		-	0.35	-	0.35	V
		$V_{CC(A)} = V_{CC(B)} = 1.4 V$						
		$I_0 = 8 \text{ mA};$		-	0.45	-	0.45	V
		$V_{CC(A)} = V_{CC(B)} = 1.65 V$			0.55		0.55	
		I <sub>O</sub> = 9 mA; V <sub>CC(A)</sub> = V <sub>CC(B)</sub> = 2.3 V		-	0.55	-	0.55	V
		$I_{O} = 12 \text{ mA};$		-	0.7	-	0.7	V
		$V_{CC(A)} = V_{CC(B)} = 3.0 V$			0.7		0.7	v
I <sub>I</sub> input leakage		nDIR, nOE input; $V_1 = 0 V \text{ or } 3.6 V$ ;		-	±1	-	±5	μA
	current	$V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$						•
BHL	bus hold	A or B port	<u>[3]</u>					
	LOW current	V <sub>I</sub> = 0.49 V;		15	-	15	-	μA
		$V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$						
		V <sub>I</sub> = 0.58 V;		25	-	25	-	μΑ
		$V_{CC(A)} = V_{CC(B)} = 1.65 V$						
		$V_{I} = 0.70 V;$		45	-	45	-	μA
		$V_{CC(A)} = V_{CC(B)} = 2.3 V$		400				
		V <sub>I</sub> = 0.80 V; V <sub>CC(A)</sub> = V <sub>CC(B)</sub> = 3.0 V		100	-	90	-	μA
	bus hold	A or B port	[4]					
BHH	HIGH current	$V_1 = 0.91 V;$		-15	-	-15	-	^
		$V_{\rm CC(A)} = V_{\rm CC(B)} = 1.4 \text{ V}$		-15	-	-15	-	μA
		$V_{\rm I} = 1.07 \text{ V};$		-25	-	-25	_	μA
		$V_{CC(A)} = V_{CC(B)} = 1.65 V$						P
		V <sub>I</sub> = 1.60 V;		-45	-	-45	-	μA
		$V_{CC(A)} = V_{CC(B)} = 2.3 V$						
		V <sub>I</sub> = 2.00 V;		-100	-	-100	-	μA
		$V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$						
BHLO	bus hold	A or B port	<u>[5]</u>					
	LOW overdrive	$V_{CC(A)} = V_{CC(B)} = 1.6 V$		125	-	125	-	μA
	current	$V_{CC(A)} = V_{CC(B)} = 1.95 V$		200	-	200	-	μA
		$V_{CC(A)} = V_{CC(B)} = 2.7 \text{ V}$		300	-	300	-	μA
		$V_{CC(A)} = V_{CC(B)} = 3.6 V$		500	-	500	-	μA
BHHO	bus hold	A or B port	<u>[6]</u>					
	HIGH	$V_{CC(A)} = V_{CC(B)} = 1.6 V$		-125	-	-125	-	μA
	overdrive current	$V_{CC(A)} = V_{CC(B)} = 1.95 V$		-200	-	-200	-	μA
	Garront	$V_{CC(A)} = V_{CC(B)} = 2.7 V$		-300	-	-300	-	μΑ
		$V_{CC(A)} = V_{CC(B)} = 3.6 V$		-500	-	-500	-	μΑ

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#### Table 8. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		–40 °C t	o +85 °C	–40 °C to	Unit	
				Min	Max	Min	Max	
l <sub>oz</sub>	OFF-state output	A or B port; $V_O = 0$ V or $V_{CCO}$ ; $V_{CC(A)} = V_{CC(B)} = 3.6$ V	[7]	-	±5	-	±30	μA
	current	suspend mode A port; $V_O = 0 V \text{ or } V_{CCO}; V_{CC(A)} = 3.6 V;$ $V_{CC(B)} = 0 V$	[7]	-	±5	-	±30	μΑ
		suspend mode B port; $V_O = 0 V \text{ or } V_{CCO}; V_{CC(A)} = 0 V;$ $V_{CC(B)} = 3.6 V$	[7]	-	±5	-	±30	μΑ
I <sub>OFF</sub> power-off leakage current	leakage	A port; V <sub>1</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC(A)</sub> = 0 V; V <sub>CC(B)</sub> = 0.8 V to 3.6 V		-	±5	-	±30	μΑ
		B port; V <sub>1</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC(B)</sub> = 0 V; V <sub>CC(A)</sub> = 0.8 V to 3.6 V		-	±5	-	±30	μΑ
СС	supply	A port; $V_I = 0 V$ or $V_{CCI}$ ; $I_O = 0 A$						
	current	$V_{CC(A)} = 0.8 V \text{ to } 3.6 V;$ $V_{CC(B)} = 0.8 V \text{ to } 3.6 V$		-	10	-	55	μA
		$V_{CC(A)} = 1.1 V \text{ to } 3.6 V;$ $V_{CC(B)} = 1.1 V \text{ to } 3.6 V$		-	8	-	50	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$		-	8	-	50	μΑ
		$V_{CC(A)} = 0 V; V_{CC(B)} = 3.6 V$		-2	-	-12	-	μA
		B port; $V_I = 0 V$ or $V_{CCI}$ ; $I_O = 0 A$						
		$V_{CC(A)} = 0.8 V \text{ to } 3.6 V;$ $V_{CC(B)} = 0.8 V \text{ to } 3.6 V$		-	10	-	55	μA
		$V_{CC(A)} = 1.1 V \text{ to } 3.6 V;$ $V_{CC(B)} = 1.1 V \text{ to } 3.6 V$		-	8	-	50	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$		-2	-	-12	-	μΑ
		$V_{CC(A)} = 0 V; V_{CC(B)} = 3.6 V$		-	8	-	50	μA
		A plus B port ( $I_{CC(A)} + I_{CC(B)}$ ); $I_{O} = 0 A$ ; $V_{I} = 0 V \text{ or } V_{CCI}$ ; $V_{CC(A)} = 0.8 V \text{ to } 3.6 V$ ; $V_{CC(B)} = 0.8 V \text{ to } 3.6 V$		-	20	-	70	μΑ
		A plus B port ( $I_{CC(A)} + I_{CC(B)}$ ); $I_{O} = 0$ A; $V_{I} = 0$ V or $V_{CCI}$ ; $V_{CC(A)} = 1.1$ V to 3.6 V; $V_{CC(B)} = 1.1$ V to 3.6 V		-	16	-	65	μΑ

[1]  $V_{CCO}$  is the supply voltage associated with the output port.

[2]  $V_{CCI}$  is the supply voltage associated with the data input port.

[3] The bus hold circuit can sink at least the minimum low sustaining current at maximum  $V_{IL}$ .  $I_{BHL}$  should be measured after lowering  $V_I$  to GND and then raising it to maximum  $V_{IL}$ .

[4] The bus hold circuit can source at least the minimum high sustaining current at minimum V<sub>IH</sub>. I<sub>BHH</sub> should be measured after raising V<sub>I</sub> to V<sub>CC</sub> and then lowering it to minimum V<sub>IH</sub>.

[5] An external driver must source at least  $I_{\mbox{\scriptsize BHLO}}$  to switch this node from LOW to HIGH.

[6] An external driver must sink at least  $I_{BHHO}$  to switch this node from HIGH to LOW.

[7] For I/O ports, the parameter  $I_{OZ}$  includes the input leakage current.

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#### 4-bit dual supply translating transceiver; 3-state

V <sub>CC(A)</sub>	V <sub>CC(B)</sub>	V <sub>CC(B)</sub>								
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V			
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μA		
0.8 V	0.1	0.1	0.1	0.1	0.1	0.3	1.6	μA		
1.2 V	0.1	0.1	0.1	0.1	0.1	0.1	0.8	μA		
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.4	μA		
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.2	μA		
2.5 V	0.1	0.3	0.1	0.1	0.1	0.1	0.1	μA		
3.3 V	0.1	1.6	0.8	0.4	0.2	0.1	0.1	μA		

#### Table 9. Typical total supply current (I<sub>CC(A)</sub> + I<sub>CC(B)</sub>)

### **11. Dynamic characteristics**

#### Table 10. Typical power dissipation capacitance at $V_{CC(A)} = V_{CC(B)}$ and $T_{amb} = 25 \text{ °C } [1][2]$ Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions			V <sub>CC(A)</sub> =	= V <sub>CC(B)</sub>			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C <sub>PD</sub> power dissipation capacitance	power dissipation capacitance	A port: (direction nAn to nBn); output enabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		A port: (direction nAn to nBn); output disabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		A port: (direction nBn to nAn); output enabled	9.5	9.7	9.8	9.9	10.7	11.9	pF
		A port: (direction nBn to nAn); output disabled	0.6	0.6	0.6	0.6	0.7	0.7	pF
		B port: (direction nAn to nBn); output enabled	9.5	9.7	9.8	9.9	10.7	11.9	pF
		B port: (direction nAn to nBn); output disabled	0.6	0.6	0.6	0.6	0.7	0.7	pF
		B port: (direction nBn to nAn); output enabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		B port: (direction nBn to nAn); output disabled	0.2	0.2	0.2	0.2	0.3	0.4	pF

[1]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu$ W).  $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$  where:

 $P_D = C_{PD} \times V_{CC}^2 \times r_i \times N + \Sigma_i$  $f_i = input frequency in MHz;$ 

 $_{i}$  = input frequency in MHz;

 $f_o =$  output frequency in MHz;

 $C_L$  = load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$  = sum of the outputs.

#### 4-bit dual supply translating transceiver; 3-state

Symbol Parameter	Parameter	Conditions	V <sub>CC(B)</sub>							
		0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V			
t <sub>pd</sub> propagation delay	nAn to nBn	14.5	7.3	6.5	6.2	5.9	6.0	ns		
		nBn to nAn	14.5	12.7	12.4	12.3	12.1	12.0	ns	
t <sub>dis</sub>	disable time	nOE to nAn	14.3	14.3	14.3	14.3	14.3	14.3	ns	
		nOE to nBn	17.0	9.9	9.0	9.4	9.0	9.7	ns	
t <sub>en</sub> enable time	nOE to nAn	18.2	18.2	18.2	18.2	18.2	18.2	ns		
		nOE to nBn	19.2	10.7	9.8	9.6	9.7	10.2	ns	

#### **Table 11.** Typical dynamic characteristics at $V_{CC(A)} = 0.8 V$ and $T_{amb} = 25 \degree C$ [1] Voltages are referenced to GND (around = 0 V): for test circuit, see Figure 8: for wave forms, see Figure 6 and Figure 7

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ ;  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ ;  $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZH}$ .

#### Table 12. Typical dynamic characteristics at $V_{CC(B)} = 0.8$ V and $T_{amb} = 25$ °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 8; for wave forms, see Figure 6 and Figure 7

Symbol	Parameter	Conditions	V <sub>CC(A)</sub>						
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t <sub>pd</sub>	t <sub>pd</sub> propagation delay	nAn to nBn	14.5	12.7	12.4	12.3	12.1	12.0	ns
		nBn to nAn	14.5	7.3	6.5	6.2	5.9	6.0	ns
t <sub>dis</sub>	disable time	nOE to nAn	14.3	5.5	4.1	4.0	3.0	3.5	ns
		nOE to nBn	17.0	13.8	13.4	13.1	12.9	12.7	ns
t <sub>en</sub>	enable time	nOE to nAn	18.2	5.6	4.0	3.2	2.4	2.2	ns
		nOE to nBn	19.2	14.6	14.1	13.9	13.7	13.6	ns

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ ;  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ ;  $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZH}$ .

#### 4-bit dual supply translating transceiver; 3-state

Symbol	Parameter	Conditions	V <sub>CC(B)</sub>									Unit	
			1.2 V ± 0.1 V		1.5 V	± 0.1 V	-	: 0.15 V	2.5 V :	± 0.2 V	3.3 V :	± 0.3 V	-
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	-
V <sub>CC(A)</sub> =	1.1 V to 1.3 V												
t <sub>pd</sub>	propagation	nAn to nBn	0.5	9.4	0.5	7.1	0.5	6.2	0.5	5.2	0.5	5.1	ns
	delay	nBn to nAn	0.5	9.4	0.5	8.9	0.5	8.7	0.5	8.4	0.5	8.2	ns
t <sub>dis</sub>	disable time	nOE to nAn	1.8	10.9	1.8	10.9	1.8	10.9	1.8	10.9	1.8	10.9	ns
		nOE to nBn	1.9	12.4	1.9	9.6	1.9	9.5	1.4	8.1	1.2	9.1	ns
t <sub>en</sub>	enable time	nOE to nAn	1.4	12.8	1.4	12.8	1.4	12.8	1.4	12.8	1.4	12.8	ns
		nOE to nBn	1.1	13.3	1.1	10.0	1.1	8.9	1.0	7.9	1.0	7.7	ns
$V_{CC(A)} =$	1.4 V to 1.6 V												_
t <sub>pd</sub>	propagation	nAn to nBn	0.3	8.9	0.3	6.3	0.3	5.2	0.3	4.2	0.3	4.2	ns
	delay	nBn to nAn	0.7	7.1	0.7	6.3	0.5	6.0	0.4	5.7	0.3	5.6	ns
t <sub>dis</sub>	disable time	n <mark>OE</mark> to nAn	1.8	10.2	1.8	10.2	1.5	10.2	1.3	10.2	1.6	10.2	ns
		nOE to nBn	1.9	11.3	1.9	10.3	1.9	9.1	1.4	7.4	1.2	7.6	ns
t <sub>en</sub>	enable time	n <mark>OE</mark> to nAn	1.1	9.4	1.4	9.4	1.1	9.4	0.7	9.4	0.4	9.4	ns
		nOE to nBn	1.4	12.1	1.4	9.6	1.1	7.7	0.9	5.8	0.9	5.6	ns
V <sub>CC(A)</sub> =	1.65 V to 1.95	V											
t <sub>pd</sub>	propagation delay	nAn to nBn	0.1	8.7	0.1	6.0	0.1	4.9	0.1	3.9	0.3	3.9	ns
		nBn to nAn	0.6	6.2	0.6	5.3	0.5	4.9	0.3	4.6	0.3	4.5	ns
t <sub>dis</sub> disa	disable time	nOE to nAn	1.8	8.6	1.6	8.6	1.8	8.6	1.3	8.6	1.6	8.6	ns
		nOE to nBn	1.7	10.9	1.7	9.9	1.6	8.7	1.2	6.9	1.0	6.9	ns
t <sub>en</sub>	enable time	nOE to nAn	1.0	7.2	1.0	7.2	1.0	7.2	0.6	7.2	0.4	7.2	ns
		nOE to nBn	1.2	11.7	1.2	9.2	1.0	7.4	0.8	5.3	0.8	4.6	ns
V <sub>CC(A)</sub> =	2.3 V to 2.7 V												
t <sub>pd</sub>	propagation	nAn to nBn	0.1	8.4	0.1	5.7	0.1	4.6	0.2	3.5	0.1	3.6	ns
	delay	nBn to nAn	0.6	5.2	0.6	4.2	0.4	3.9	0.2	3.4	0.2	3.3	ns
t <sub>dis</sub>	disable time	nOE to nAn	1.0	6.2	1.0	6.2	1.0	6.2	1.0	6.2	1.0	6.2	ns
		nOE to nBn	1.5	10.4	1.5	8.8	1.3	8.2	1.1	6.2	0.9	5.2	ns
t <sub>en</sub>	enable time	n <mark>OE</mark> to nAn	0.7	4.8	0.7	4.8	0.7	4.8	0.6	4.8	0.4	4.8	ns
		nOE to nBn	0.9	11.3	0.9	8.8	0.8	7.0	0.6	4.8	0.6	4.0	ns
$V_{CC(A)} =$	3.0 V to 3.6 V												_
t <sub>pd</sub>	propagation	nAn to nBn	0.1	8.2	0.1	5.6	0.1	4.5	0.1	3.3	0.1	2.9	ns
	delay	nBn to nAn	0.6	5.1	0.6	4.2	0.4	3.4	0.2	3.0	0.1	2.8	ns
t <sub>dis</sub>	disable time	n <mark>OE</mark> to nAn	0.7	5.6	0.7	5.6	0.7	5.6	0.7	5.6	0.7	5.6	ns
		nOE to nBn	1.4	10.2	1.4	9.3	1.2	8.1	1.0	6.4	0.8	6.2	ns
t <sub>en</sub>	enable time	n <mark>OE</mark> to nAn	0.6	3.8	0.6	3.8	0.6	3.8	0.6	3.8	0.4	3.8	ns
		nOE to nBn	0.8	11.3	0.8	8.7	0.6	6.8	0.5	4.7	0.5	3.8	ns

### Table 13. Dynamic characteristics for temperature range -40 °C to +85 °C [1]Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 8; for wave forms, see Figure 6 and Figure 7.

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ ;  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ ;  $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZH}$ .

#### 4-bit dual supply translating transceiver; 3-state

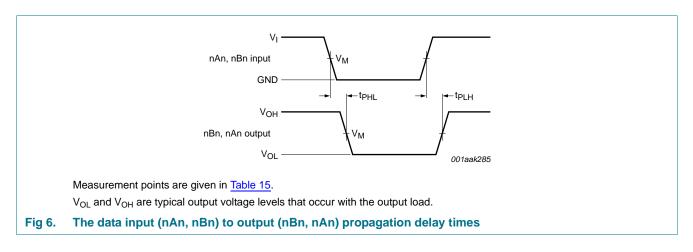
Symbol	Parameter	Conditions					٧c	C(B)					Unit
			1.2 V :	± 0.1 V	1.5 V :	± 0.1 V		: 0.15 V	2.5 V :	± 0.2 V	3.3 V :	± 0.3 V	1
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	_
$V_{CC(A)} =$	1.1 V to 1.3 V												
t <sub>pd</sub>	propagation	nAn to nBn	0.5	10.4	0.5	7.9	0.5	6.9	0.5	5.8	0.5	5.7	ns
	delay	nBn to nAn	0.5	10.4	0.5	9.8	0.5	9.6	0.5	9.3	0.5	9.1	ns
t <sub>dis</sub>	disable time	nOE to nAn	1.8	12.0	1.8	12.0	1.8	12.0	1.8	12.0	1.8	12.0	ns
		nOE to nBn	1.9	13.7	1.9	10.6	1.9	10.5	1.4	9.0	1.2	10.1	ns
t <sub>en</sub>	enable time	nOE to nAn	1.4	14.1	1.4	14.1	1.4	14.1	1.4	14.1	1.4	14.1	ns
		nOE to nBn	1.1	14.7	1.1	11.0	1.1	9.8	1.0	8.7	1.0	8.5	ns
V <sub>CC(A)</sub> =	1.4 V to 1.6 V												
t <sub>pd</sub>	propagation	nAn to nBn	0.3	9.8	0.3	7.0	0.3	5.8	0.3	4.7	0.3	4.7	ns
	delay	nBn to nAn	0.7	7.9	0.7	7.0	0.5	6.6	0.4	6.3	0.3	6.2	ns
t <sub>dis</sub>	disable time	nOE to nAn	1.8	11.3	1.8	11.3	1.5	11.3	1.3	11.3	1.6	11.3	ns
		nOE to nBn	1.9	12.5	1.9	11.4	1.9	10.1	1.4	8.2	1.2	8.4	ns
t <sub>en</sub>	enable time	nOE to nAn	1.1	10.4	1.4	10.4	1.1	10.4	0.7	10.4	0.4	10.4	ns
		nOE to nBn	1.4	13.3	1.4	10.6	1.1	8.5	0.9	6.4	0.9	6.2	ns
V <sub>CC(A)</sub> =	1.65 V to 1.95	V											
t <sub>pd</sub> propag delay	propagation	nAn to nBn	0.1	9.6	0.1	6.6	0.1	5.4	0.1	4.3	0.3	4.3	ns
	delay	nBn to nAn	0.6	6.9	0.6	5.9	0.5	5.4	0.3	5.1	0.3	5.0	ns
t <sub>dis</sub> d	disable time	n <mark>OE</mark> to nAn	1.8	9.5	1.6	9.5	1.8	9.5	1.3	9.5	1.6	9.5	ns
		n <mark>OE</mark> to nBn	1.7	12.0	1.7	10.9	1.6	9.6	1.2	7.6	1.0	7.6	ns
t <sub>en</sub>	enable time	nOE to nAn	1.0	8.0	1.0	8.0	1.0	8.0	0.6	8.0	0.4	8.0	ns
		nOE to nBn	1.2	12.9	1.2	10.2	1.0	8.2	0.8	5.9	0.8	5.1	ns
V <sub>CC(A)</sub> =	2.3 V to 2.7 V												
t <sub>pd</sub>	propagation	nAn to nBn	0.1	9.3	0.1	6.3	0.1	5.1	0.2	4.0	0.1	4.0	ns
	delay	nBn to nAn	0.6	5.8	0.6	4.7	0.4	4.3	0.2	3.9	0.2	3.8	ns
t <sub>dis</sub>	disable time	n <mark>OE</mark> to nAn	1.0	6.9	1.0	6.9	1.0	6.9	1.0	6.9	1.0	6.9	ns
		nOE to nBn	1.5	11.5	1.5	10.4	1.3	9.1	1.1	6.9	0.9	5.8	ns
t <sub>en</sub>	enable time	nOE to nAn	0.7	5.3	0.7	5.3	0.7	5.3	0.6	5.3	0.4	5.3	ns
		nOE to nBn	0.9	12.4	0.9	9.7	0.8	7.7	0.6	5.3	0.6	4.4	ns
V <sub>CC(A)</sub> =	3.0 V to 3.6 V												
t <sub>pd</sub>	propagation	nAn to nBn	0.1	9.1	0.1	6.2	0.1	5.0	0.1	3.8	0.1	3.3	ns
	delay	nBn to nAn	0.6	5.7	0.6	4.7	0.4	3.9	0.2	3.4	0.1	3.3	ns
t <sub>dis</sub>	disable time	nOE to nAn	0.7	6.2	0.7	6.2	0.7	6.2	0.7	6.2	0.7	6.2	ns
		nOE to nBn	1.4	11.3	1.4	10.3	1.2	9.0	1.0	7.1	0.8	6.9	ns
t <sub>en</sub>	enable time	nOE to nAn	0.6	4.2	0.6	4.2	0.6	4.2	0.6	4.2	0.4	4.2	ns
		nOE to nBn	0.8	12.4	0.8	9.6	0.6	7.5	0.5	5.2	0.5	4.2	ns

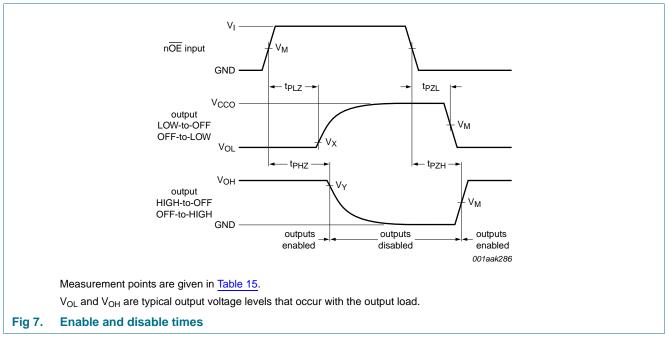
#### **Table 14.** Dynamic characteristics for temperature range -40 °C to +125 °C 11Voltages are referenced to GND (ground = 0.01); for test circuit, see Figure 8: for wave forms, see Figure 6 and Figure 7.

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ ;  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ ;  $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZH}$ .

4-bit dual supply translating transceiver; 3-state

### 12. Waveforms





#### Table 15. Measurement points

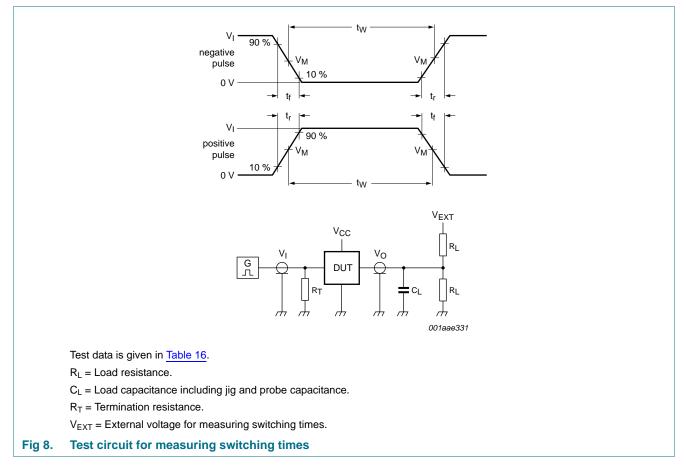
Supply voltage	Input <sup>[1]</sup>	Output <sup>[2]</sup>		
V <sub>CC(A)</sub> , V <sub>CC(B)</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>
0.8 V to 1.6 V	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.1 V	V <sub>OH</sub> – 0.1 V
1.65 V to 2.7 V	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.15 V	V <sub>OH</sub> – 0.15 V
3.0 V to 3.6 V	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.3 V	V <sub>OH</sub> – 0.3 V

[1]  $V_{CCI}$  is the supply voltage associated with the data input port.

[2]  $V_{CCO}$  is the supply voltage associated with the output port.

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#### 4-bit dual supply translating transceiver; 3-state



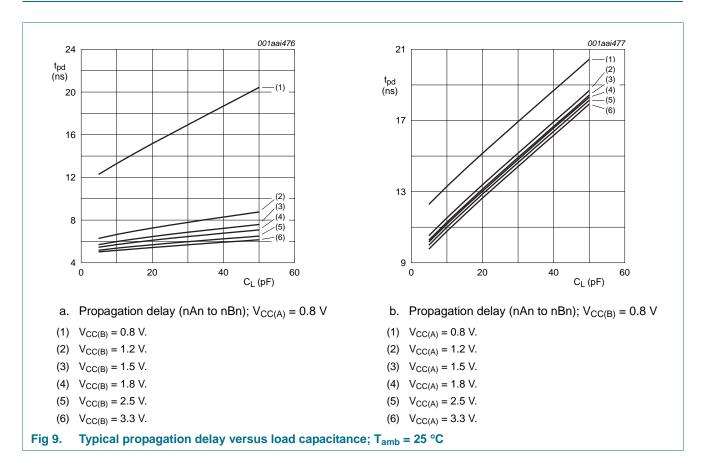
#### Table 16. Test data

Supply voltage	Input		Load		V <sub>EXT</sub>		
V <sub>CC(A)</sub> , V <sub>CC(B)</sub>	V <sub>I</sub> [1]	∆t/∆V <sup>[2]</sup>	CL	RL	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ<sup>[3]</sup></sub>
0.8 V to 1.6 V	V <sub>CCI</sub>	$\leq$ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V <sub>CCO</sub>
1.65 V to 2.7 V	V <sub>CCI</sub>	$\leq$ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V <sub>CCO</sub>
3.0 V to 3.6 V	V <sub>CCI</sub>	$\leq$ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V <sub>CCO</sub>

[1]  $V_{CCI}$  is the supply voltage associated with the data input port.

[3]  $V_{CCO}$  is the supply voltage associated with the output port.

4-bit dual supply translating transceiver; 3-state

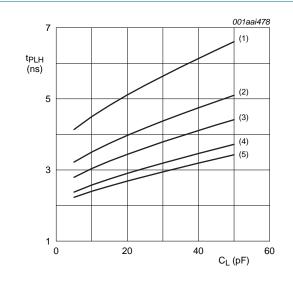


### 13. Typical propagation delay characteristics

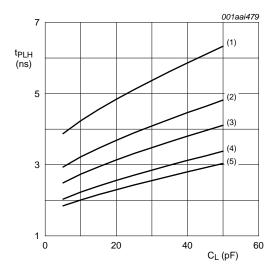
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# 74AVCH4T245-Q100

#### 4-bit dual supply translating transceiver; 3-state

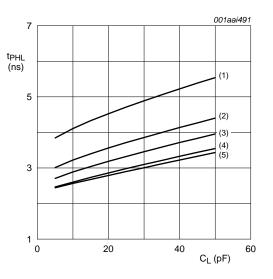


a. LOW to HIGH propagation delay (nAn to nBn);  $V_{CC(A)}$  = 1.2 V

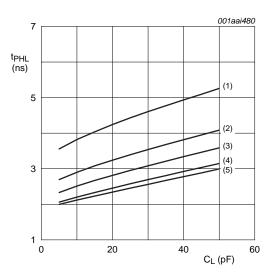


- c. LOW to HIGH propagation delay (nAn to nBn);  $V_{CC(A)} = 1.5 \text{ V}$
- (1)  $V_{CC(B)} = 1.2$  V.
- (2) V<sub>CC(B)</sub> = 1.5 V.
- (3)  $V_{CC(B)} = 1.8$  V.
- (4)  $V_{CC(B)} = 2.5 V.$
- (5)  $V_{CC(B)} = 3.3 V.$

Fig 10. Typical propagation delay versus load capacitance; T<sub>amb</sub> = 25 °C



b. HIGH to LOW propagation delay (nAn to nBn);  $V_{CC(A)} = 1.2 \text{ V}$ 

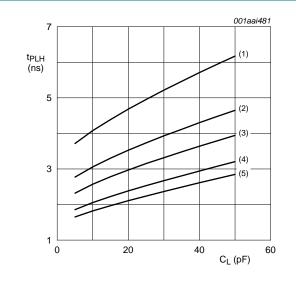


d. HIGH to LOW propagation delay (nAn to nBn);  $V_{CC(A)} = 1.5 \text{ V}$ 

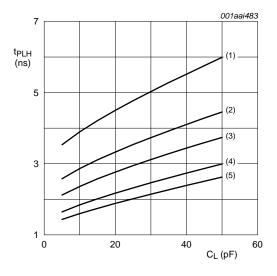
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# 74AVCH4T245-Q100

#### 4-bit dual supply translating transceiver; 3-state

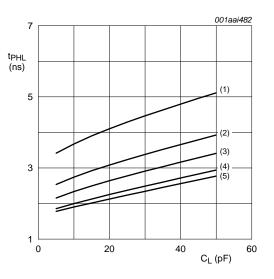


a. LOW to HIGH propagation delay (nAn to nBn);  $V_{CC(A)}$  = 1.8 V

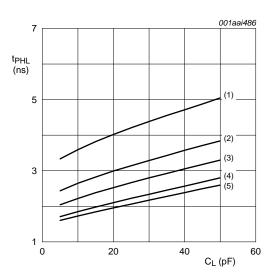


- c. LOW to HIGH propagation delay (nAn to nBn);  $V_{CC(A)}$  = 2.5 V
- (1)  $V_{CC(B)} = 1.2$  V.
- (2) V<sub>CC(B)</sub> = 1.5 V.
- (3)  $V_{CC(B)} = 1.8$  V.
- (4)  $V_{CC(B)} = 2.5 V.$
- (5)  $V_{CC(B)} = 3.3 V.$

Fig 11. Typical propagation delay versus load capacitance;  $T_{amb} = 25 \text{ °C}$ 



b. HIGH to LOW propagation delay (nAn to nBn);  $V_{CC(A)} = 1.8 \text{ V}$ 

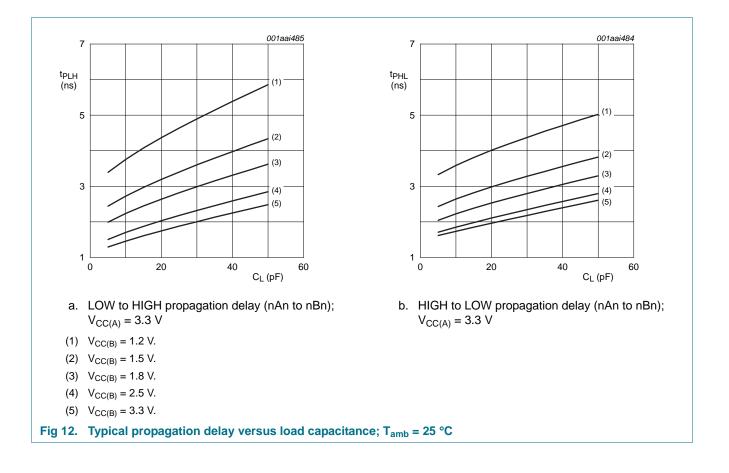


d. HIGH to LOW propagation delay (nAn to nBn);  $V_{CC(A)} = 2.5 \text{ V}$ 

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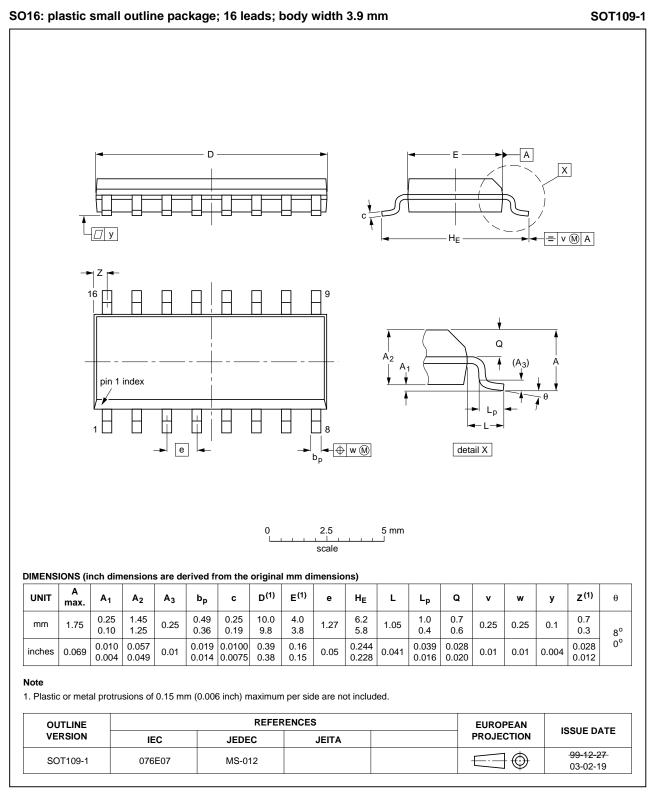
# 74AVCH4T245-Q100

4-bit dual supply translating transceiver; 3-state



4-bit dual supply translating transceiver; 3-state

### 14. Package outline



#### Fig 13. Package outline SOT109-1 (SO16)

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Product data sheet

All information

4-bit dual supply translating transceiver; 3-state

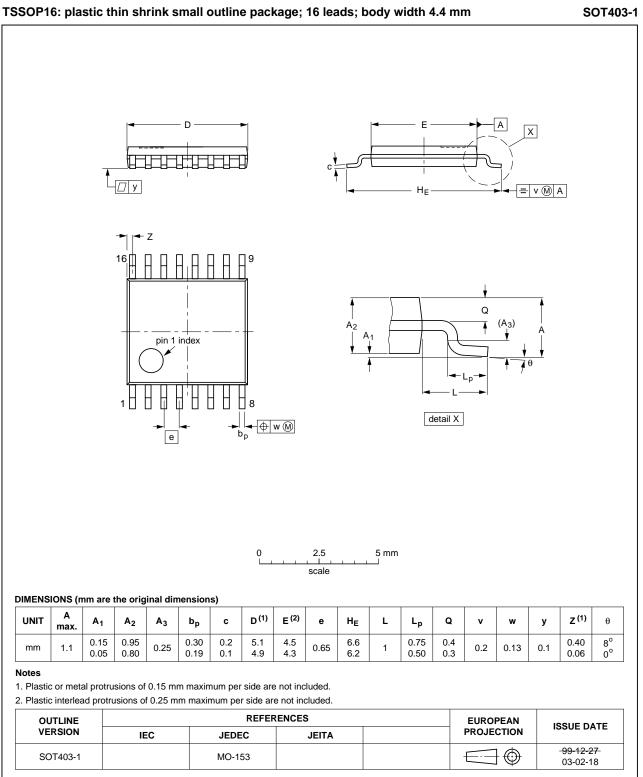
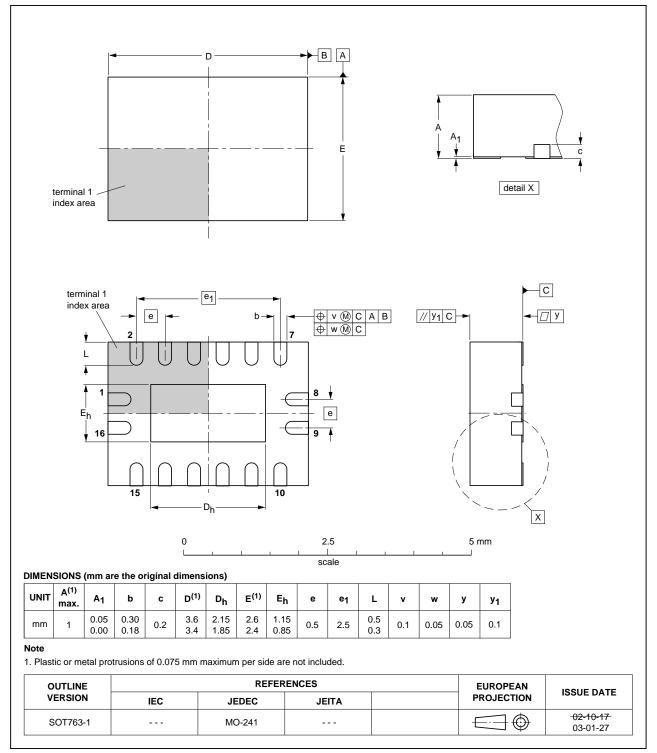


Fig 14. Package outline SOT403-1 (TSSOP16)

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DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

#### Fig 15. Package outline SOT763-1 (DHVQFN16)

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4-bit dual supply translating transceiver; 3-state

### **15. Abbreviations**

Table 17. Abbreviations					
Acronym	Description				
CDM	Charged Device Model				
DUT	Device Under Test				
ESD	ElectroStatic Discharge				
HBM	Human Body Model				
MM	Machine Model				
MIL	Military				

### 16. Revision history

#### Table 18. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74AVCH4T245_Q100 v.2	20151217	Product data sheet	-	74AVCH4T245_Q100 v.1	
Modifications:       • Table 5: conditions I <sub>CC</sub> and I <sub>GND</sub> changed (errata).					
74AVCH4T245_Q100 v.1	20130916	Product data sheet	-	-	

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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